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CONFIRMATION NO. APPLICATION NO. FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO. 09/12/2003 10/660,821 Feng-Yu Yeh 07942.0029 7043 7590 EXAMINER 06/15/2005 Finnegan, Henderson, Farabow, CHEN, KIN CHAN Garrett & Dunner, L.L.P. PAPER NUMBER 1300 I Street, N.W. ART UNIT Washington, DC 20005-3315 1765

DATE MAILED: 06/15/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
Office Action Summary	10/660,821	YEH ET AL.	
	Examiner	Art Unit	
	Kin-Chan Chen	1765	
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply			
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).			
Status			
1) Responsive to communication(s) filed on			
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3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is			
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.			
Disposition of Claims			
4)⊠ Claim(s) <u>1-19</u> is/are pending in the application.			
4a) Of the above claim(s) is/are withdrawn from consideration.			
5)⊠ Claim(s) <u>1-4 and 6-17</u> is/are allowed.			
6)⊠ Claim(s) <u>5 and 18</u> is/are rejected.			
7)⊠ Claim(s) <u>19</u> is/are objected to.			
8) Claim(s) are subject to restriction and/or election requirement.			
Application Papers			
9)⊠ The specification is objected to by the Examine	r.		
10)⊠ The drawing(s) filed on <u>12 September 2003</u> is/are: a) accepted or b)⊠ objected to by the Examiner.			
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).			
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).			
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.			
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).			
a) ☐ All b) ☐ Some * c) ☐ None of:			
1. Certified copies of the priority documents have been received.			
2. Certified copies of the priority documents have been received in Application No			
3. Copies of the certified copies of the priority documents have been received in this National Stage			
application from the International Bureau (PCT Rule 17.2(a)).			
* See the attached detailed Office action for a list of the certified copies not received.			
Attachment(s)			
1) Notice of References Cited (PTO-892)	4) Interview Summary		
<ul> <li>2) Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)</li> <li>Paper No(s)/Mail Date <u>082704</u>.</li> </ul>	Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ite atent Application (PTO-152)	
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### **DETAILED ACTION**

### Specification

1. The disclosure is objected to because of the following informalities:

In the specification, page 7, line 7, "etchant" includes an acid such as  $NH_4OH/H_2O_2$  is incorrect because  $NH_4OH/H_2O_2$  is not an acid.

Appropriate correction is required.

## Claim Objections

2. Claim 19 is objected to because of the following informalities:

The specification is objected to as failing to provide proper antecedent basis for the claimed subject matter. See 37 CFR 1.75(d)(1) and MPEP § 608.01(o). Correction of the following is required:

In claim 19, "a temperature ranging from approximately 55 °C to **7** °C" is not described in the specification.

Claim Rejections - 35 USC § 112

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3. Claims 5 and 18 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

In claim 5, "the etching of the remaining tungsten silicide layer uses an acid" is vague and indefinite because in light of the specification applicants set forth the process using NH<sub>4</sub>OH/H<sub>2</sub>O<sub>2</sub> which is not an acid.

In claim 18, "the second etchant includes NH<sub>4</sub>OH/H<sub>2</sub>O<sub>2</sub>"is vague and indefinite because in light of the specification applicants set forth the process using an acid.

#### Allowable Subject Matter

- 4. Claims 1-4 and 6-17 are allowed.
- 5. The following is an examiner's statement of reasons for allowance:

The references of record do not teach or suggest a method comprising:

After etching the remaining tungsten silicide with a second etchant, annealing the tungsten silicide layer, etching the exposed polycrystalline silicon layer; and oxidizing sidewalls of the tungsten silicide and polycrystalline silicon layer (applicable to claims 1 and 8).

After partially etching the tungsten silicide with a first etchant, annealing the tungsten silicide layer, etching the remaining tungsten silicide with a second etchant,

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etching the exposed polycrystalline silicon layer; and oxidizing sidewalls of the tungsten silicide and polycrystalline silicon layer (applicable to claim 16).

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kin-Chan Chen whose telephone number is (571) 272-1461. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

June 9, 2005

Kin-Chan Chen Primary Examiner Art Unit 1765